Pin Description

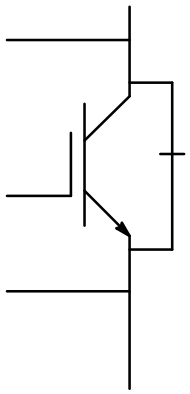


Figure 1. Pin Description

MODULE CHARACTERISTICS (T_{vj} = 25°C, Unless Otherwise Specified)

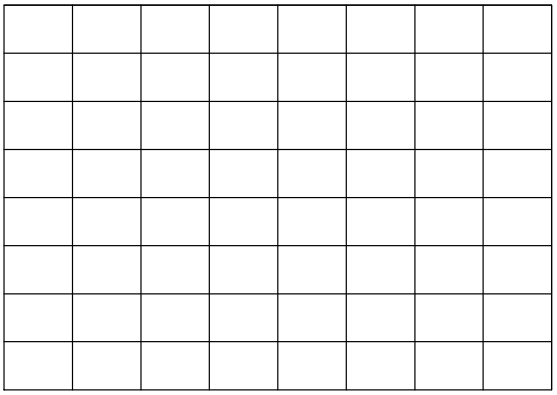
Symbol	Parameter	Rating	Unit
T_{vj}	Operating Junction Temperature	−40 to 175	°C
T_{STG}	Storage Temperature	−40 to 125	°C
V_{ISO}	Isolation Voltage (DC, 0 Hz, 1 s)	4200	V
L_{sCE}	Stray Inductance	8	nH
RCC'+EE'	Module Lead Resistance, Terminals − Chip	0.75	mΩ
G	Module Weight		

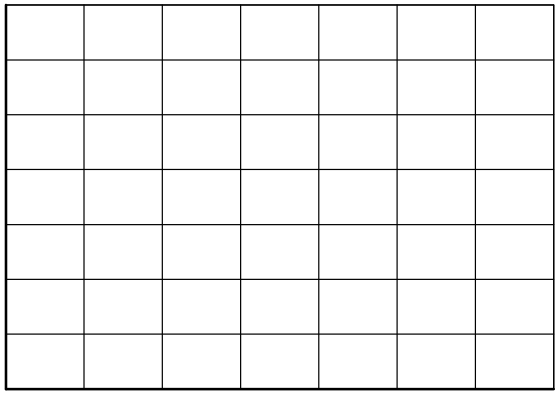
CHARACTERISTICS OF IGBT (T_{vj} = 25°C, Unless Otherwise Specified)

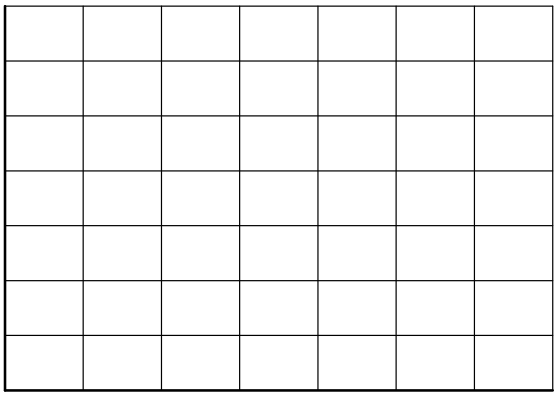
Symbol	Parameters	Conditions		Min	Typ	Max	Unit
V_{CESAT}	Collector to Emitter Saturation Voltage (Terminal)	V_{GE} = 15 V, I_C = 600 A	T_{vj} = 25°C	–	1.30	1.55	V
	Collector to Emitter Saturation Voltage (Chip)	V					

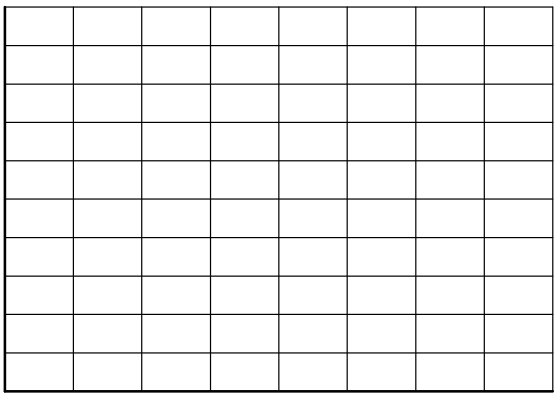
CHARACTERISTICS OF INVERSE DIODE (T_{vj} = 25

TYPICAL CHARACTERISTICS









VE

TYPICAL CHARACTERISTICS

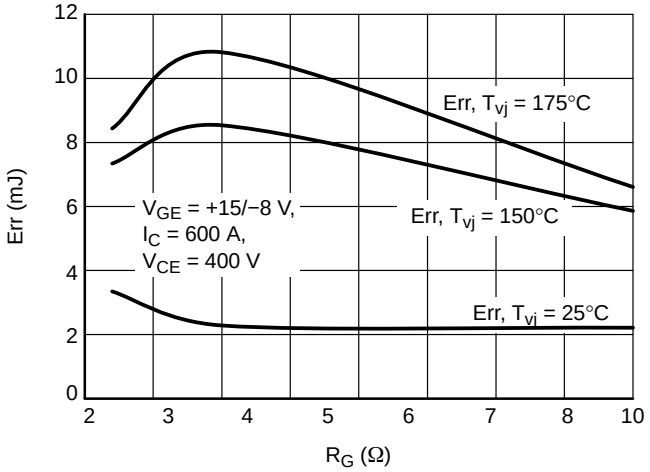


Figure 14. Diode Switching Losses vs. R_G

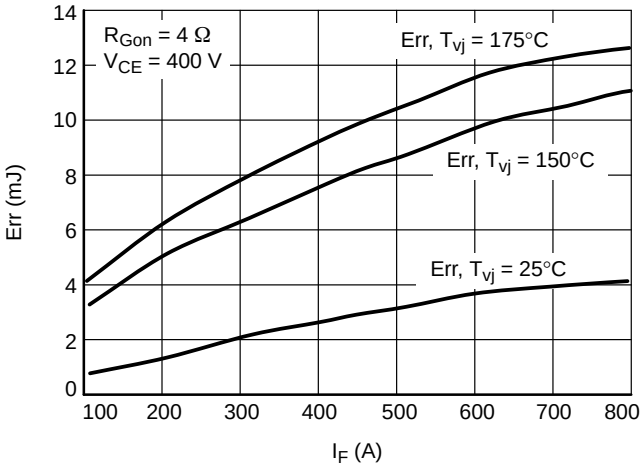
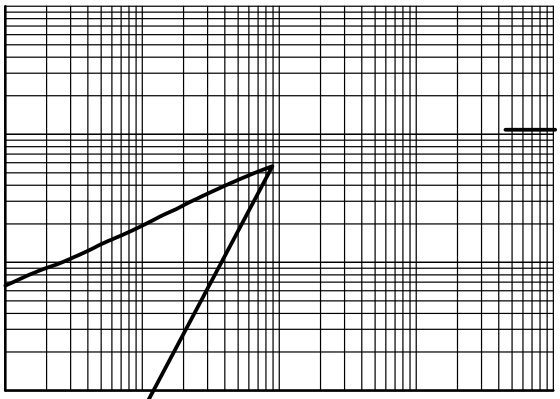
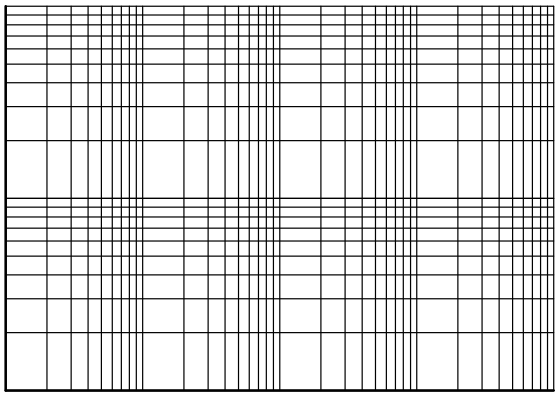
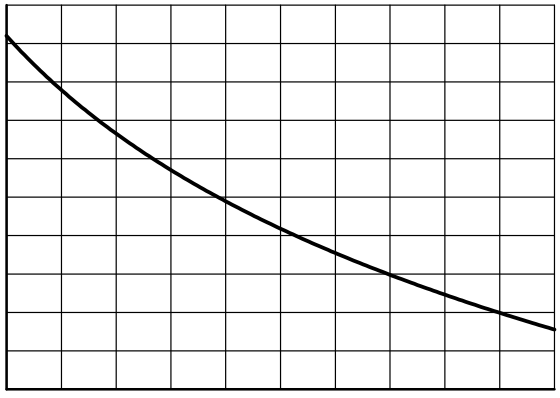


Figure 15. Diode Switching Losses vs. I_F







SSDC33, 154.50x92.0 (SPB)
CASE 183AB
ISSUE A

DATE 05 DEC 2019

XXXXX = Specific Device Code
G = Pb−Free Package
AT = Assembly & Test Site Code
YYWW= Year and Work Week Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “